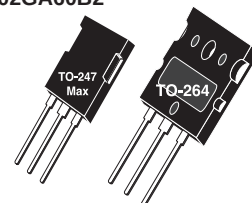


High Speed PT IGBT

POWER MOS 8® is a high speed Punch-Through switch-mode IGBT. Low E_{off} is achieved through leading technology silicon design and lifetime control processes. A reduced E_{off} - $V_{CE(ON)}$ tradeoff results in superior efficiency compared to other IGBT technologies. Low gate charge and a greatly reduced ratio of C_{res}/C_{ies} provide excellent noise immunity, short delay times and simple gate drive. The intrinsic chip gate resistance and capacitance of the poly-silicone gate structure help control di/dt during switching, resulting in low EMI, even when switching at high frequency.

APT102GA60B2



APT102GA60L

Single die IGBT



FEATURES

- Fast switching with low EMI
- Very Low E_{off} for maximum efficiency
- Ultra low C_{res} for improved noise immunity
- Low conduction loss
- Low gate charge
- Increased intrinsic gate resistance for low EMI
- RoHS compliant 

TYPICAL APPLICATIONS

- ZVS phase shifted and other full bridge
- Half bridge
- High power PFC boost
- Welding
- UPS, solar, and other inverters
- High frequency, high efficiency industrial

Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
V_{CES}	Collector Emitter Voltage	600	V
I_{C1}	Continuous Collector Current @ $T_c = 25^\circ\text{C}$ ¹	183	A
I_{C2}	Continuous Collector Current @ $T_c = 100^\circ\text{C}$	102	
I_{CM}	Pulsed Collector Current ²	307	
V_{GE}	Gate-Emitter Voltage ³	±30	V
P_D	Total Power Dissipation @ $T_c = 25^\circ\text{C}$	780	W
SSOA	Switching Safe Operating Area @ $T_j = 150^\circ\text{C}$	307A @ 600V	
T_j, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Lead Temperature for Soldering: 0.063" from Case for 10 Seconds	300	

Static Characteristics

 $T_j = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{BR(CES)}$	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 250\mu\text{A}$	600			V
$V_{CE(on)}$	Collector-Emitter On Voltage	$V_{GE} = 15V, I_C = 62A$ $T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$		2.0 1.9	2.5	
$V_{GE(th)}$	Gate Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1mA$	3	4.5	6	
I_{CES}	Zero Gate Voltage Collector Current	$V_{CE} = 600V, V_{GE} = 0V$ $T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$			1000 5000	μA
I_{GES}	Gate-Emitter Leakage Current	$V_{GS} = \pm 30V$			±100	nA

Thermal and Mechanical Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction to Case Thermal Resistance	-	-	0.16	$^\circ\text{C/W}$
W_T	Package Weight	-	5.9	-	g
Torque	Mounting Torque (TO-247 Package), 4-40 or M3 screw			10	in·lbf

Dynamic Characteristics

$T_J = 25^{\circ}\text{C}$ unless otherwise specified

APT102GA60B2_L

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	Capacitance $V_{GE} = 0\text{V}$, $V_{CE} = 25\text{V}$ $f = 1\text{MHz}$		8170		pF
C_{oes}	Output Capacitance			630		
C_{res}	Reverse Transfer Capacitance			78		
Q_g^4	Total Gate Charge	Gate Charge $V_{GE} = 15\text{V}$ $V_{CE} = 300\text{V}$ $I_C = 62\text{A}$		294		nC
Q_{ge}	Gate-Emitter Charge			56		
Q_{gc}	Gate- Collector Charge			106		
SSOA	Switching Safe Operating Area	$T_J = 150^{\circ}\text{C}$, $R_G = 4.7\Omega^5$, $V_{GE} = 15\text{V}$, $L = 100\mu\text{H}$, $V_{CE} = 600\text{V}$	307			A
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching (25°C) IGBT and Diode $V_{CC} = 400\text{V}$ $V_{GE} = 15\text{V}$ $I_C = 62\text{A}$ $R_G = 4.7\Omega^5$ $T_J = +25^{\circ}\text{C}$		28		ns
t_r	Current Rise Time			37		
$t_{d(off)}$	Turn-Off Delay Time			212		
t_f	Current Fall Time			101		
E_{on2}	Turn-On Switching Energy			1354		μJ
E_{off}^7	Turn-Off Switching Energy			1614		
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching (125°C) IGBT and Diode $V_{CC} = 400\text{V}$ $V_{GE} = 15\text{V}$ $I_C = 62\text{A}$ $R_G = 4.7\Omega^5$ $T_J = +125^{\circ}\text{C}$		27		ns
t_r	Current Rise Time			37		
$t_{d(off)}$	Turn-Off Delay Time			247		
t_f	Current Fall Time			142		
E_{on2}	Turn-On Switching Energy			2106		μJ
E_{off}^7	Turn-Off Switching Energy			1852		

1 Continuous current limited by package lead temperature.

2 Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature.

3 Pulse test: Pulse Width $< 380\mu\text{s}$, duty cycle $< 2\%$.

4 See Mil-Std-750 Method 3471.

5 R_G is external gate resistance, not including internal gate resistance or gate driver impedance. (MIC4452)

6 E_{on2} is the clamped inductive turn on energy that includes a commutating diode reverse recovery current in the IGBT turn on energy loss. A combi device is used for the clamping diode.

7 E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1.

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

Typical Performance Curves

APT102GA60B2_L

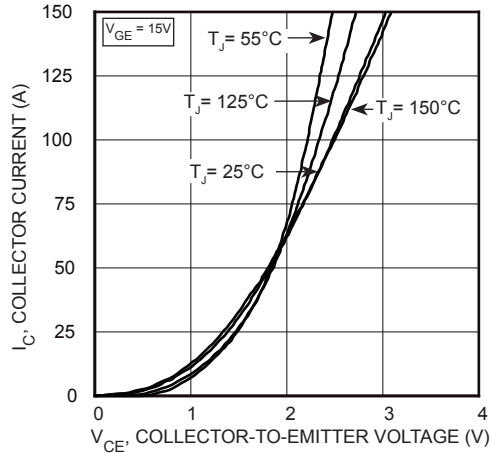


FIGURE 1, Output Characteristics ($T_J = 25^\circ\text{C}$)

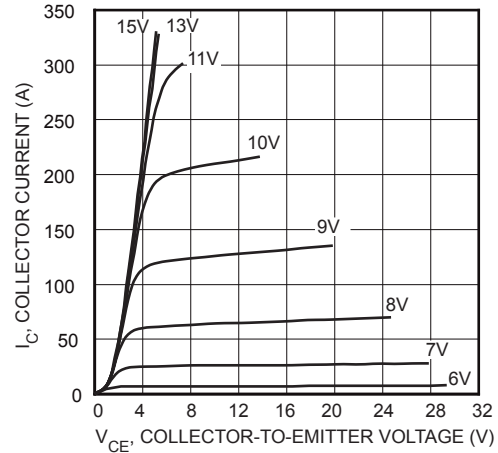


FIGURE 2, Output Characteristics ($T_J = 25^\circ\text{C}$)

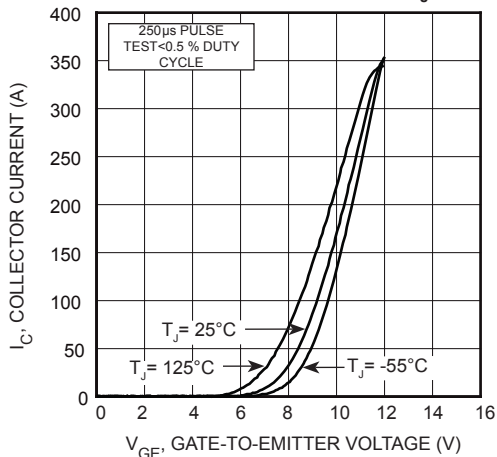


FIGURE 3, Transfer Characteristics

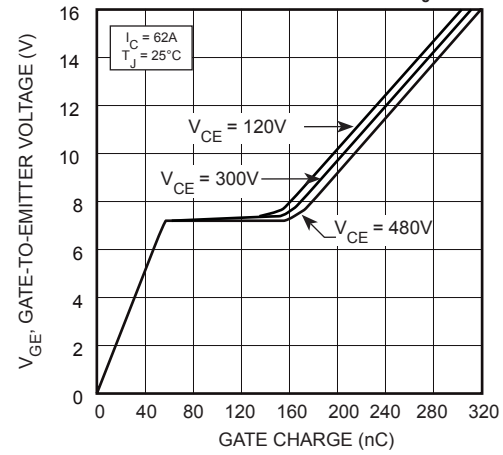


FIGURE 4, Gate charge

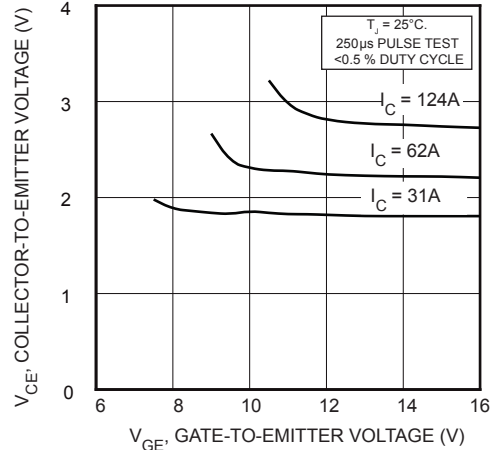


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

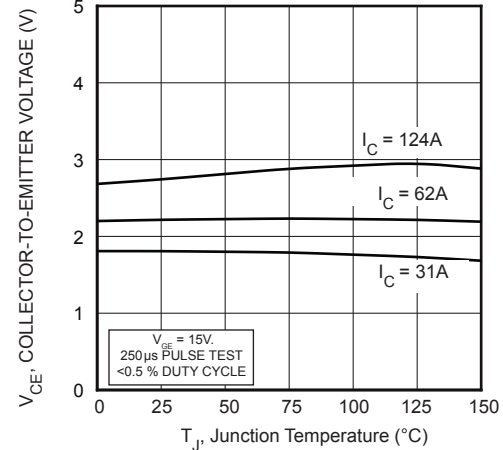


FIGURE 6, On State Voltage vs Junction Temperature

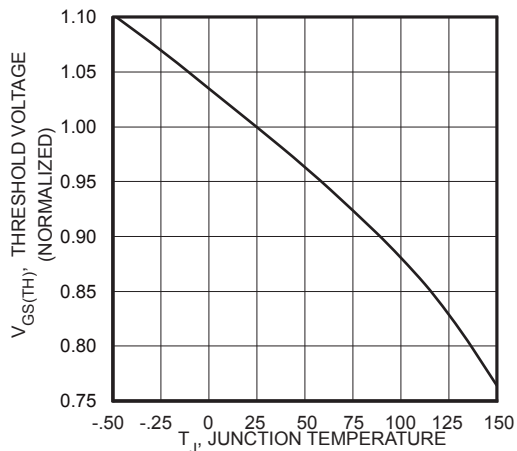


FIGURE 7, Threshold Voltage vs Junction Temperature

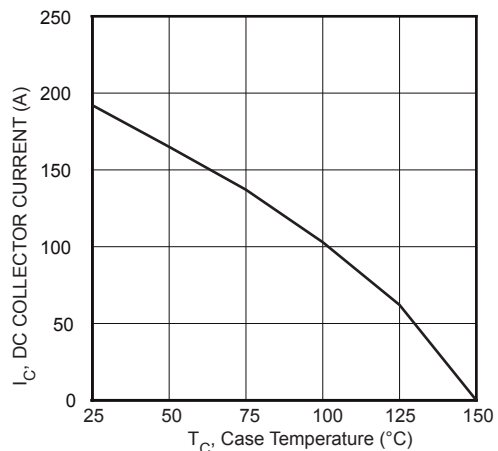


FIGURE 8, DC Collector Current vs Case Temperature

Typical Performance Curves

APT102GA60B2_L

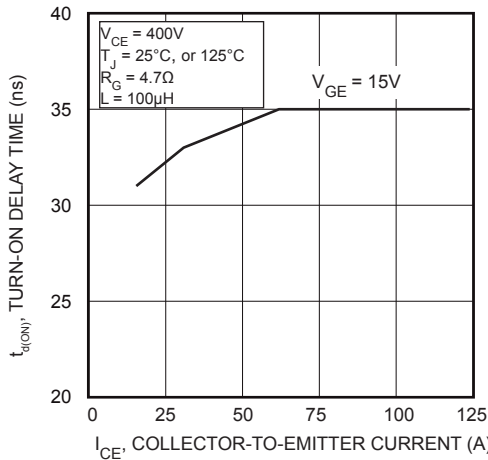


FIGURE 9, Turn-On Delay Time vs Collector Current

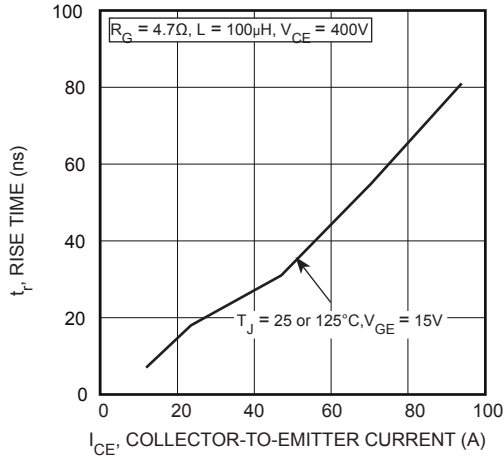


FIGURE 11, Current Rise Time vs Collector Current

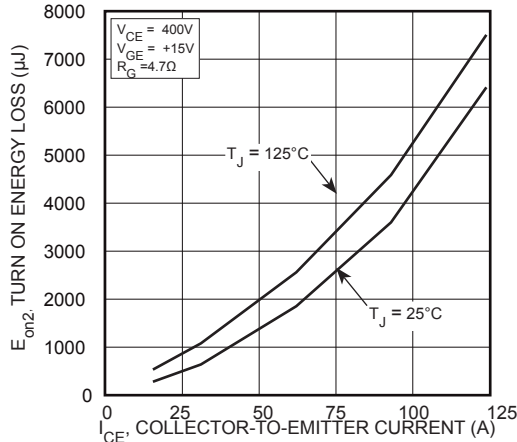


FIGURE 13, Turn-On Energy Loss vs Collector Current

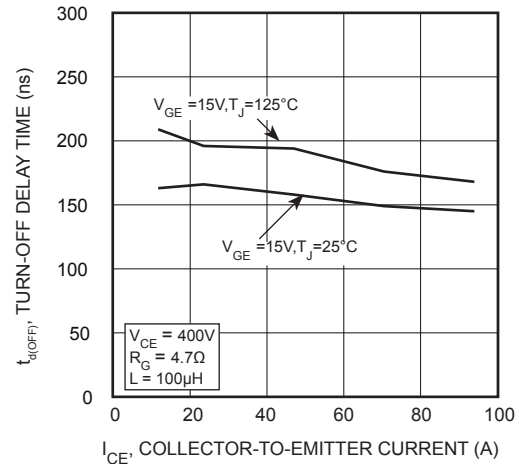


FIGURE 10, Turn-Off Delay Time vs Collector Current

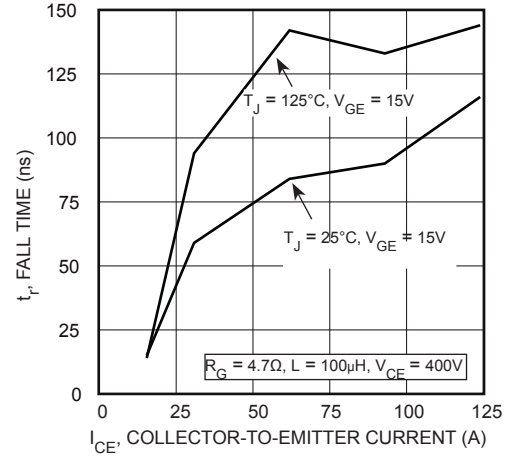


FIGURE 12, Current Fall Time vs Collector Current

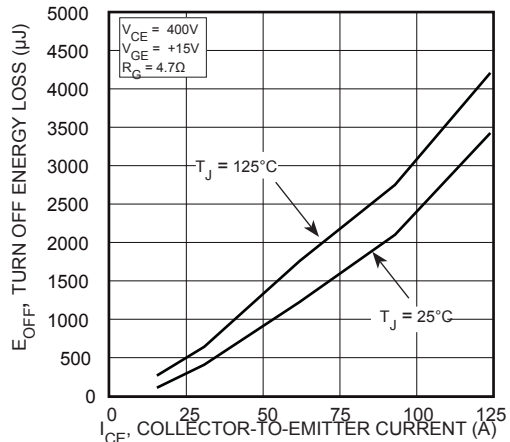


FIGURE 14, Turn-Off Energy Loss vs Collector Current

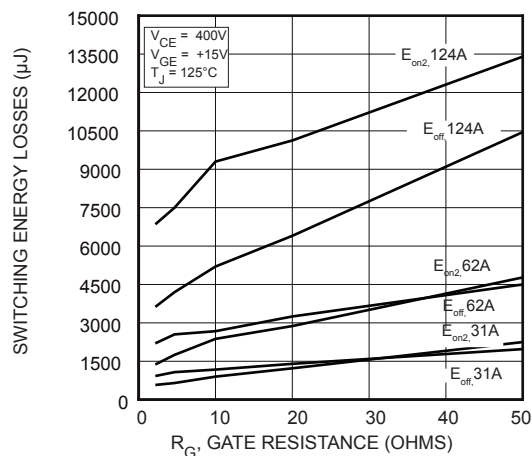


FIGURE 15, Switching Energy Losses vs Gate Resistance

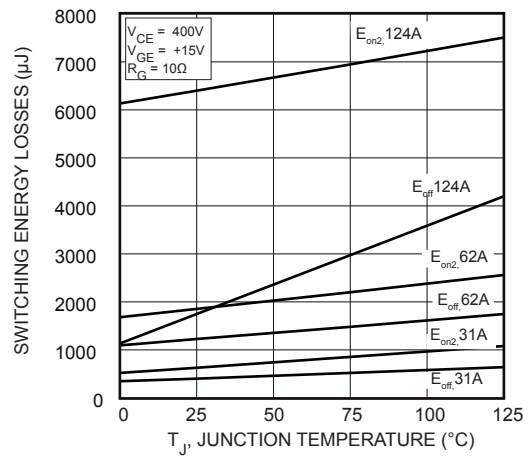


FIGURE 16, Switching Energy Losses vs Junction Temperature

Typical Performance Curves

APT102GA60B2_L

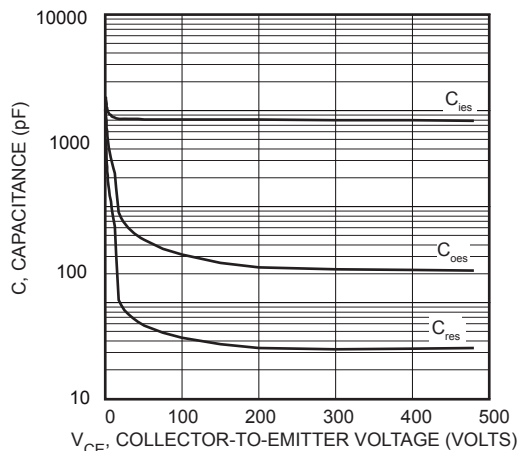


FIGURE 17, Capacitance vs Collector-To-Emitter Voltage

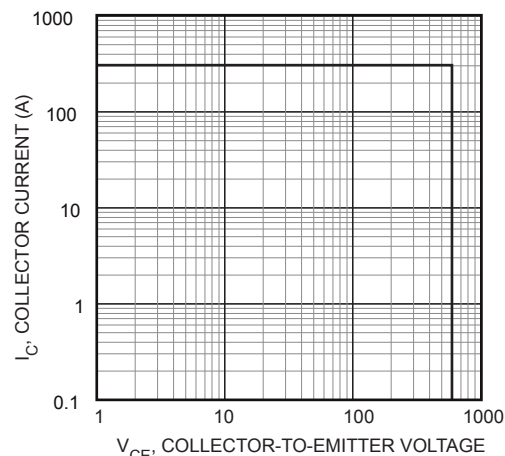


FIGURE 18, Minimum Switching Safe Operating Area

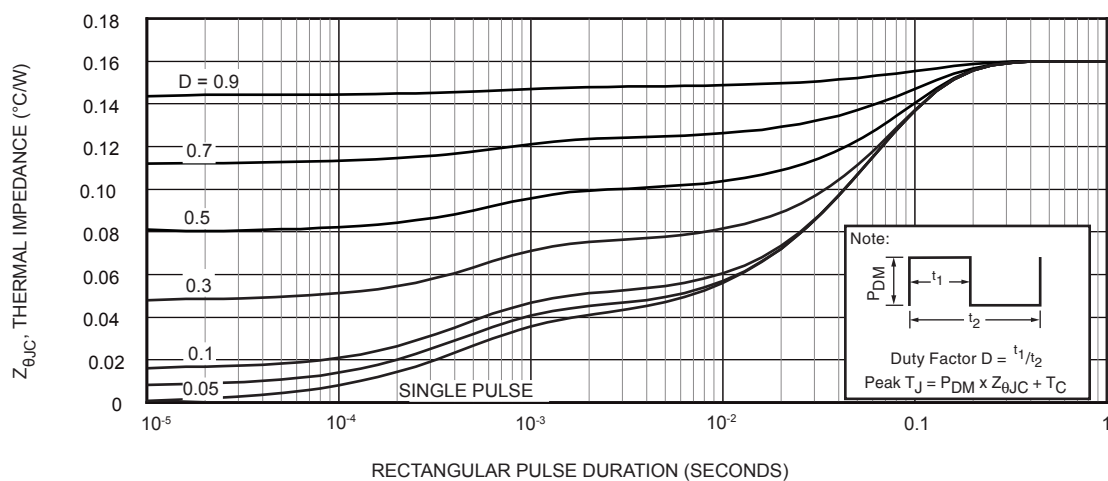


Figure 19a, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

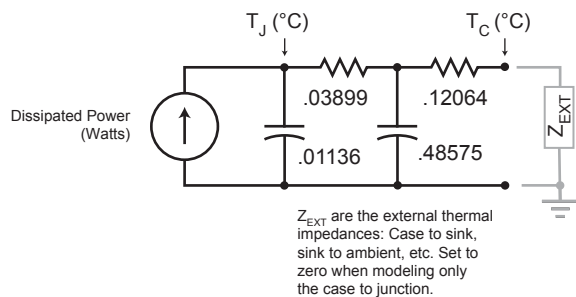


FIGURE 19b, TRANSIENT THERMAL IMPEDANCE MODEL

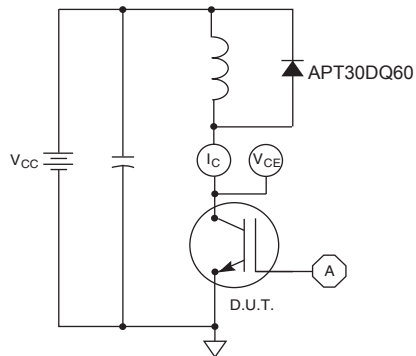


Figure 20, Inductive Switching Test Circuit

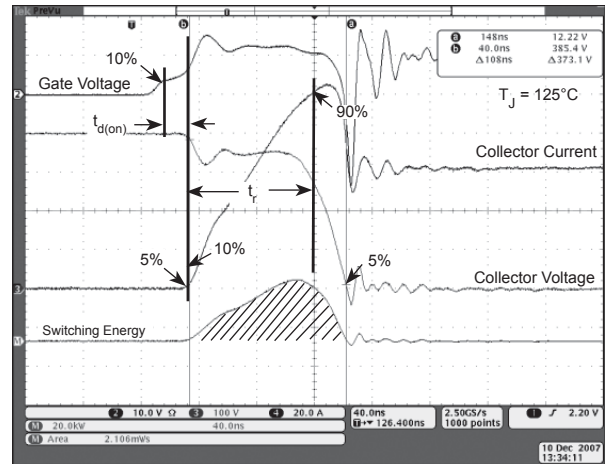


Figure 21, Turn-on Switching Waveforms and Definitions

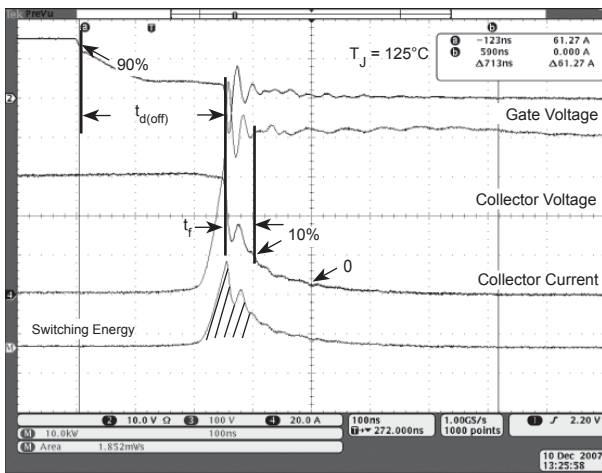
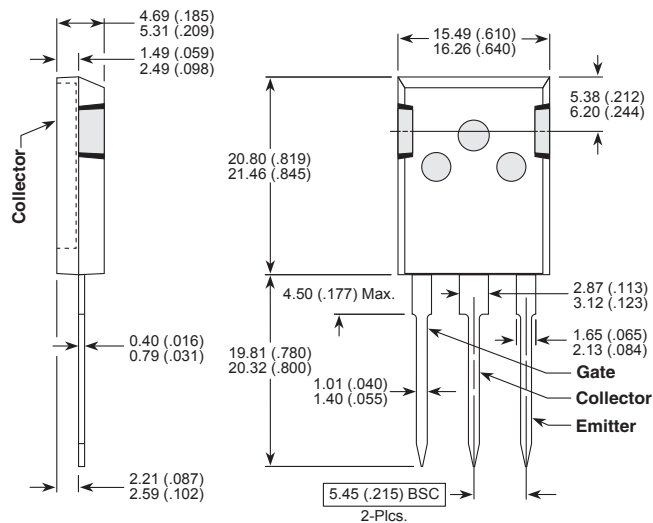


Figure 22, Turn-off Switching Waveforms and Definitions

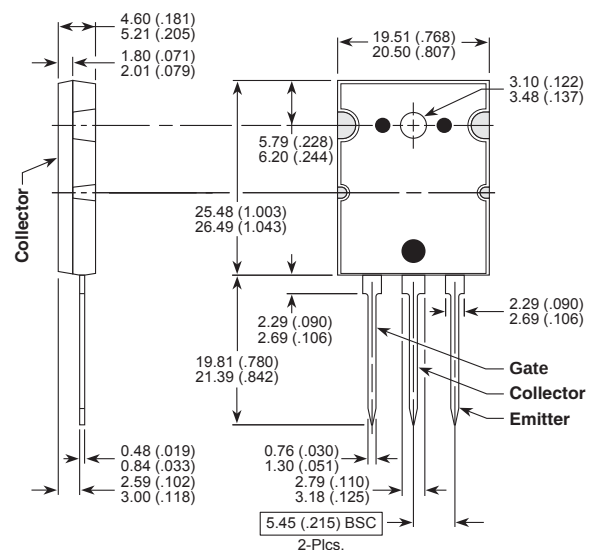
T-MAX™ (B2) Package Outline



These dimensions are equal to the TO-247 without the mounting hole.

Dimensions in Millimeters and (Inches)

TO-264 (L) Package Outline



Dimensions in Millimeters and (Inches)

Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 6,939,743, 7,352,045 5,283,201 5,801,417 5,648,283 7,196,634 6,664,594 7,157,886 6,939,743 7,342,262 and foreign patents. US and Foreign patents pending. All Rights Reserved.